

Supplementary Information for  
Oxynitrides: Enabling Photoelectrochemical Water Splitting  
with over 3,000 hrs Stable Operation in Practical Two-Electrode  
Configuration

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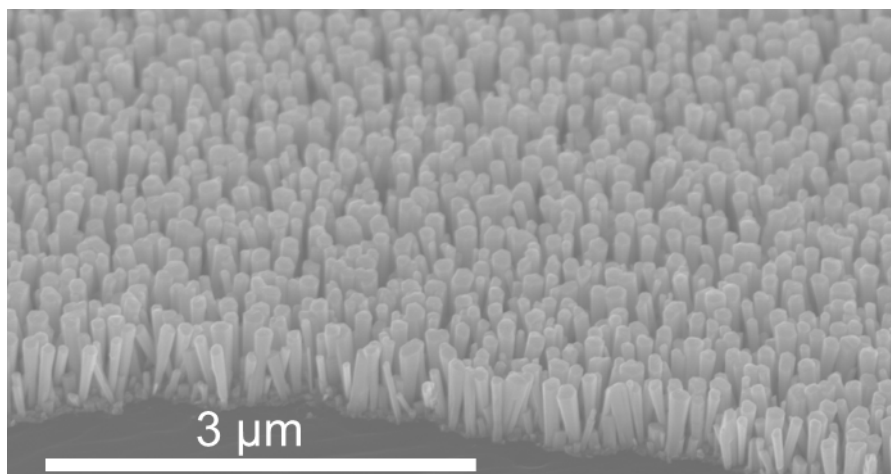
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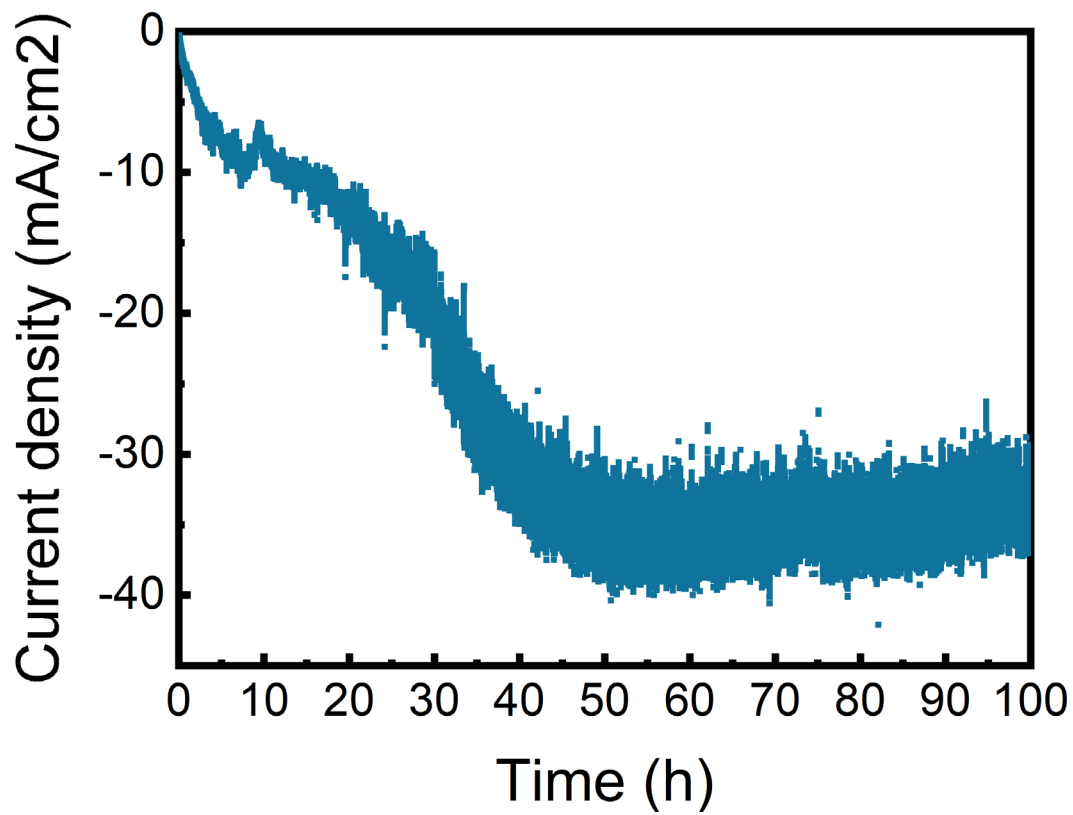
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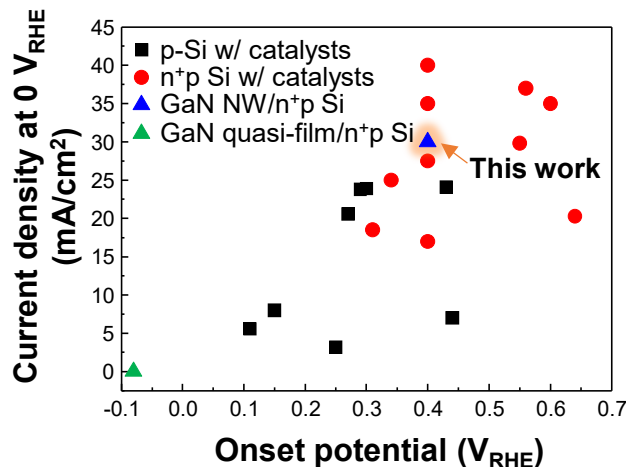


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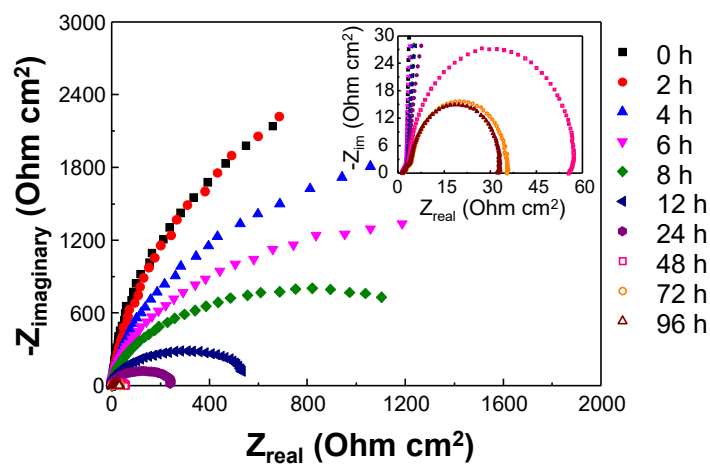
20 **Figure S1.** Scanning electron micrograph of the as-grown  $n^+$ -GaN nanowires/Si photocathode.



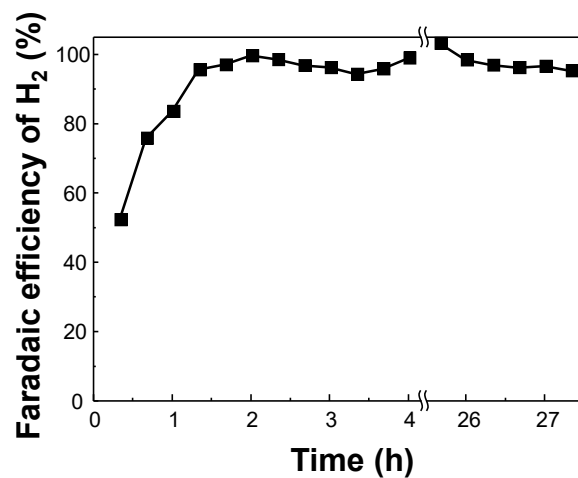
**Figure S2.** Chronoamperometry (CA) curve of the GaN NW/Si photocathode at -0.4 V vs. reversible hydrogen electrode under AM 1.5G one-sun illumination in 0.5 M H<sub>2</sub>SO<sub>4</sub>.



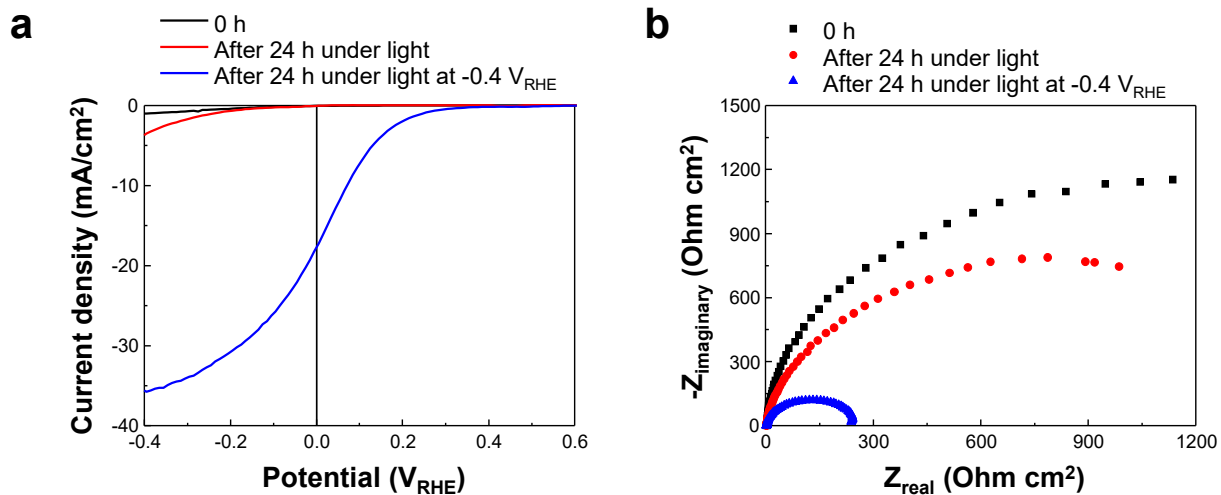
**Figure S3.** Performance comparison of Si photocathodes for  $H_2$  evolution reaction. The Y-axis indicates the photocurrent density at 0 V vs. reversible hydrogen electrode ( $V_{RHE}$ ) and the X-axis indicates the onset potential ( $V_{on}$ ).  $n^+p$  Si photocathodes with catalysts (red circles) show better performance than  $p$ -type Si photocathodes with catalysts (black squares). Notably, GaN NW/Si (this work, highlighted blue triangle) shows a significant advancement from the previous GaN quasi-film/Si photocathode (green triangle)<sup>1</sup> due to the beneficial nanowire morphology of GaN.



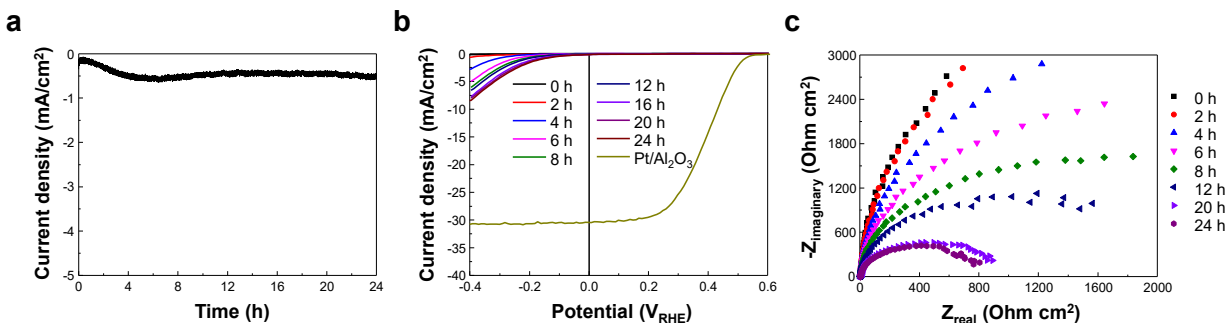
**Figure S4.** Photoelectrochemical Nyquist impedance plots of GaN NW/Si after the CA test for each period time (0 – 96 h). The measurements were conducted at -0.4 V<sub>RHE</sub> under AM 1.5G 1 sun light illumination. Inset shows a magnified graph of the low resistance region.



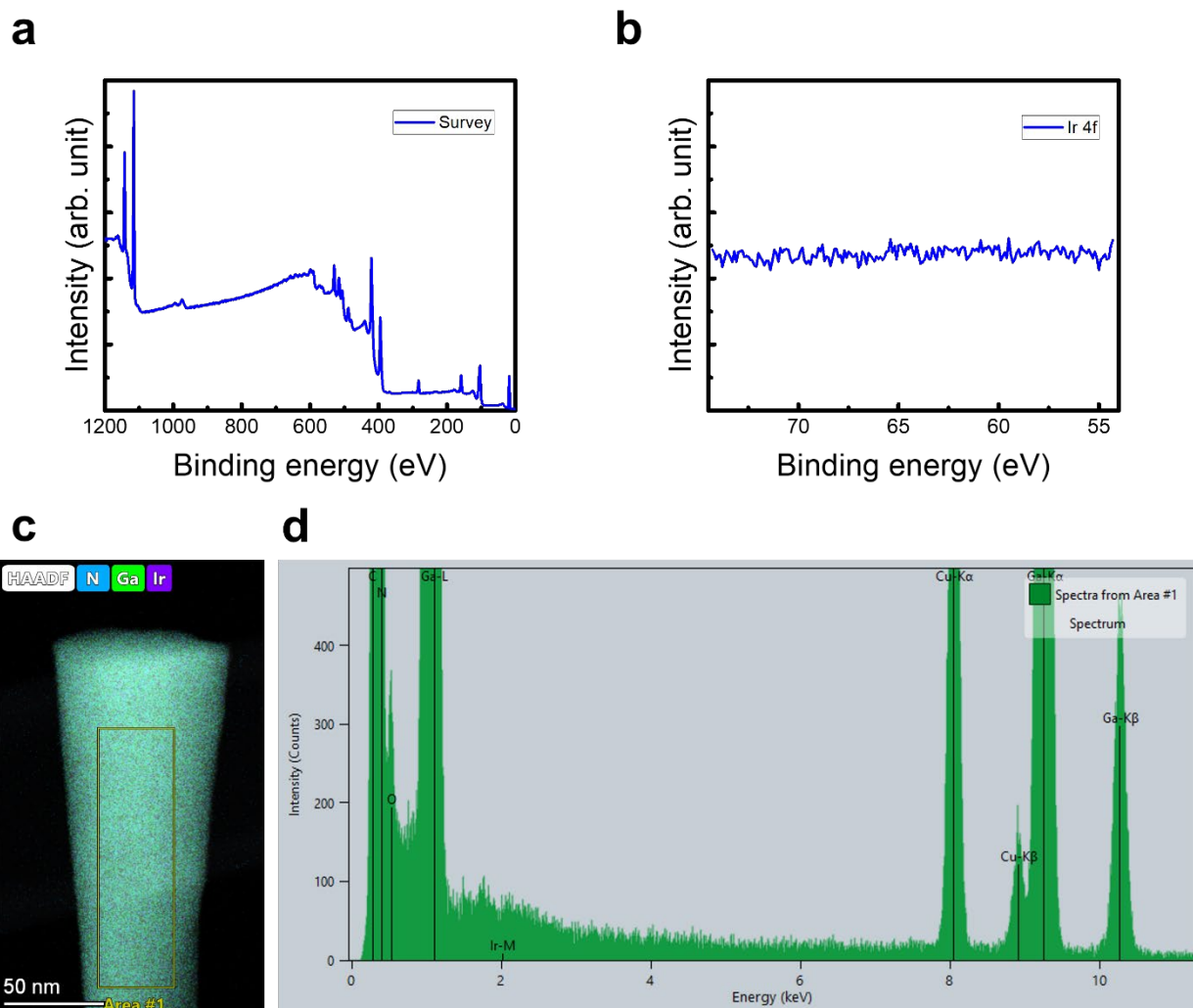
**Figure S5.** Faradaic efficiency of H<sub>2</sub> measured at -0.4 V<sub>RHE</sub> for initial 4 h and after CA test (25 h). The measurements were taken at -0.4 V<sub>RHE</sub> under AM 1.5G 1 sun light illumination.



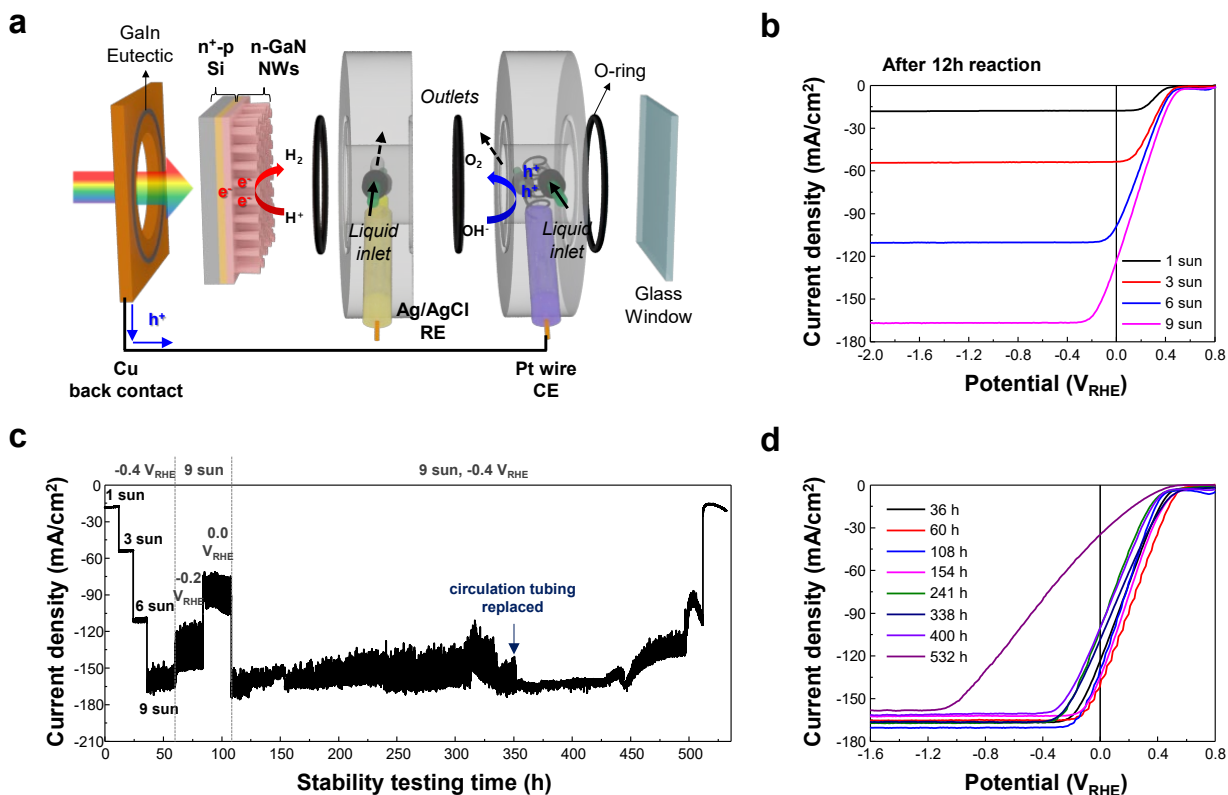
**Figure S6.** (a) Linear sweep voltammetry curves and (b) Nyquist plots of GaN NW/Si photocathodes; pristine (0 h, black), under one-sun illumination at open-circuit potential (24 h, red), and under one-sun illumination at -0.4 V<sub>RHE</sub> (24 h, blue). Both light illumination and cathodic potential are required for the self-improvement of GaN NW/Si photocathode.



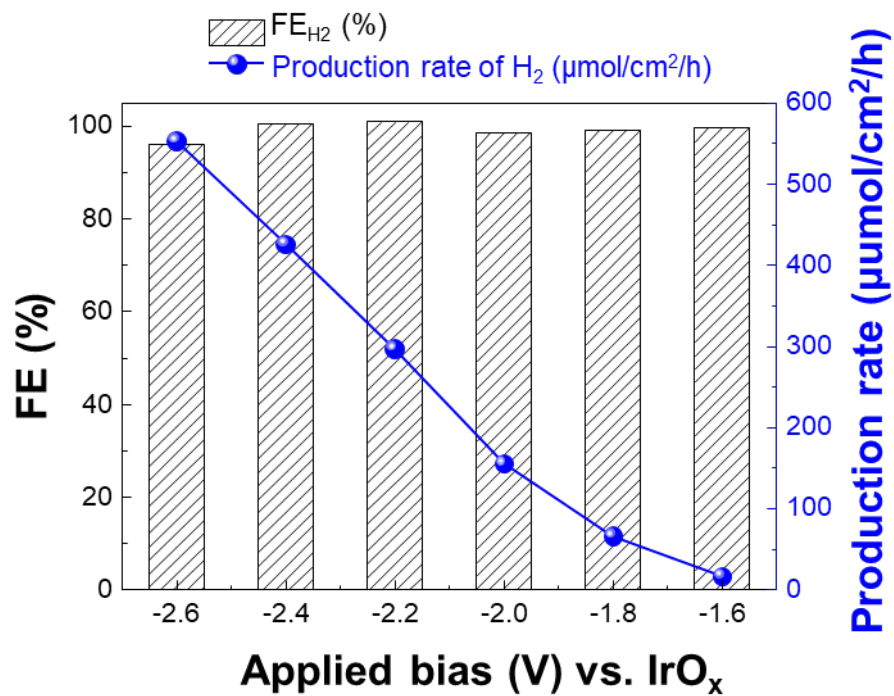
**Figure S7.** (a) CA curve, (b) LSV curves, and (c) Nyquist impedance plots of Al<sub>2</sub>O<sub>3</sub> (2 nm)-passivated GaN NW/Si photocathodes. There was very little increase in photocurrent density and decrease in charge transfer resistance after 24 hours of reaction at -0.4 V<sub>RHE</sub> under one-sun illumination. Even after 24 hours of chronoamperometry, the negative V<sub>on</sub> (< 0 V<sub>RHE</sub>) and the small photocurrent density (< 10 mA/cm<sup>2</sup> at -0.4 V<sub>RHE</sub>) clearly demonstrate that the performance is not as good as GaN NW/Si (V<sub>on</sub> > 0 V<sub>RHE</sub> and the photocurrent density > 30 mA/cm<sup>2</sup> at -0.4 V<sub>RHE</sub>). Panel (b) also shows that, after a routine photodeposition of Pt cocatalysts, the activity of the Al<sub>2</sub>O<sub>3</sub> passivated photocathode is comparable to one without Al<sub>2</sub>O<sub>3</sub> passivation (after Pt deposition).



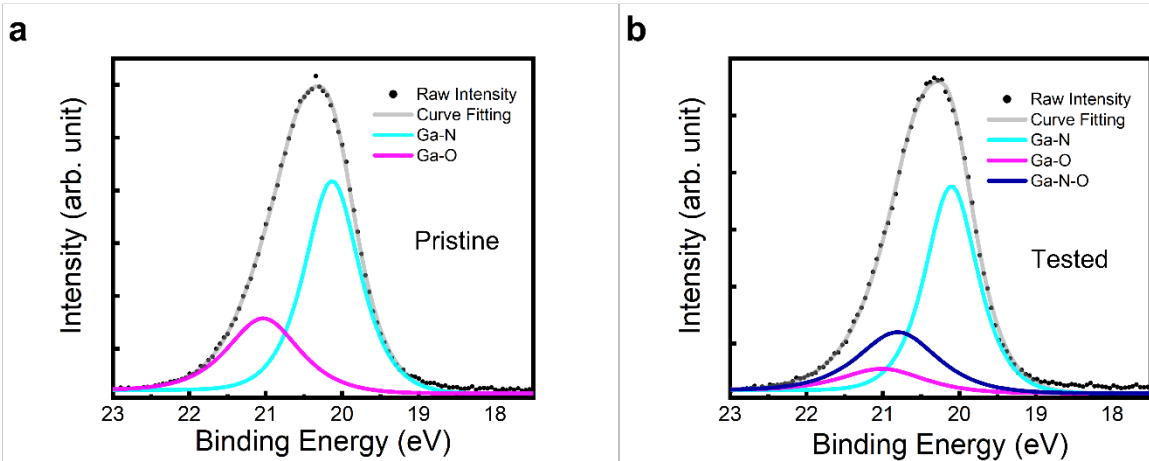
**Figure S8.** (a) Survey spectrum of X-ray photoelectron spectroscopy (XPS) of the GaN NW/Si photocathode after 48 hours of chronoamperometry at  $-0.4 V_{RHE}$  under one-sun illumination. (b) XPS of the GaN NW/Si photocathode shows no Ir after 48 hours of chronoamperometry at  $-0.4 V_{RHE}$  under one-sun illumination. (c) Region of interest for the Transmission electron microscopy (TEM) energy dispersive X-ray spectroscopy (EDS) spectrum is given by the box with yellow outlines and label "Area #1". (d) The TEM EDS spectrum in the region of interest shows no Ir after reaction with conditions given above.



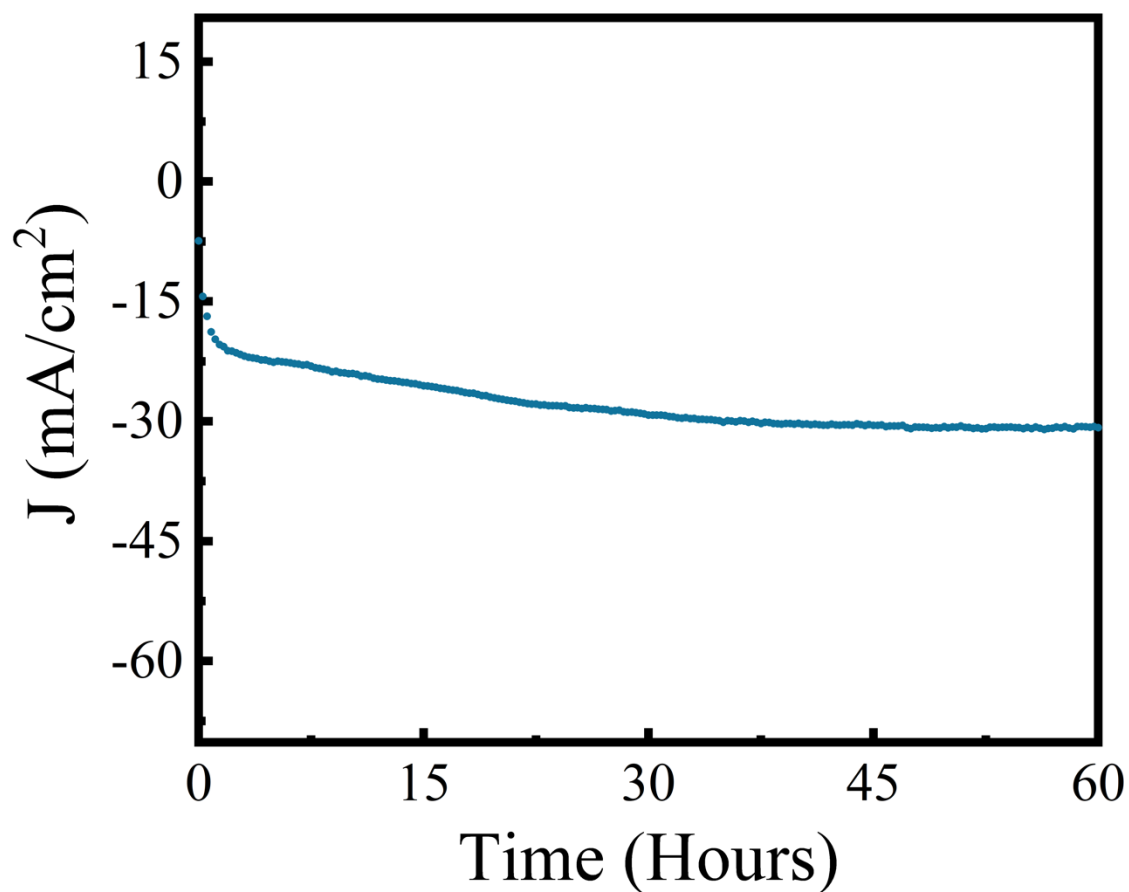
**Figure S9.** (a) Schematic illustration of the flow cell for concentrated solar light photoelectrochemical H<sub>2</sub> evolution reaction. Simulated solar spectrum is irradiated on the backside of Si wafer and reaction takes place on the front side of GaN NWs. Electrolyte was continuously flowed with a rate of 28 ml/min. (b) LSV curves of CA-tested GaN NW/Si for 12 h under nine-sun illumination. The saturated photocurrent densities linearly correlate to the light intensity. (c) CA curves measured at different light intensities and potentials. (d) LSV curves of GaN NW/Si after the CA test for each period time (0 – 532 h) under the concentrated solar light (9 sun).



**Figure S10.** Faradaic efficiency of the GaN NW/Si photoelectrode at different biases after 24 hr of chronoamperometry at -2 V vs. IrO<sub>x</sub> under one-sun illumination.

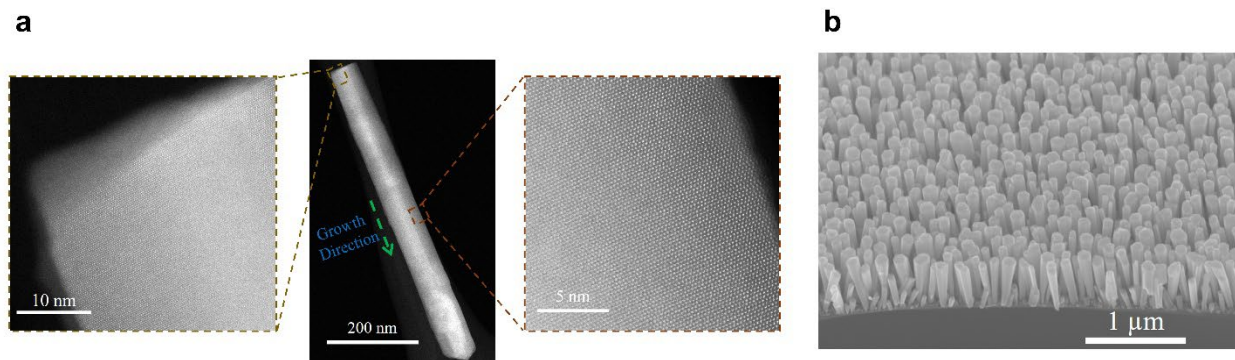


**Figure S11.** XPS measurements for *Ga 3d* of pristine (0 h) sample (a) showing deconvoluted peaks at 20.2 eV and 21 eV for Ga-N (cyan curve) and Ga-O (magenta curve), respectively. The curve fitting of the raw XPS data is the gray curve. *Ga 3d* peaks of the tested (after 10 h) sample (b) show an additional deconvoluted peak at 20.8 eV corresponding to gallium oxynitride species (navy blue curve).

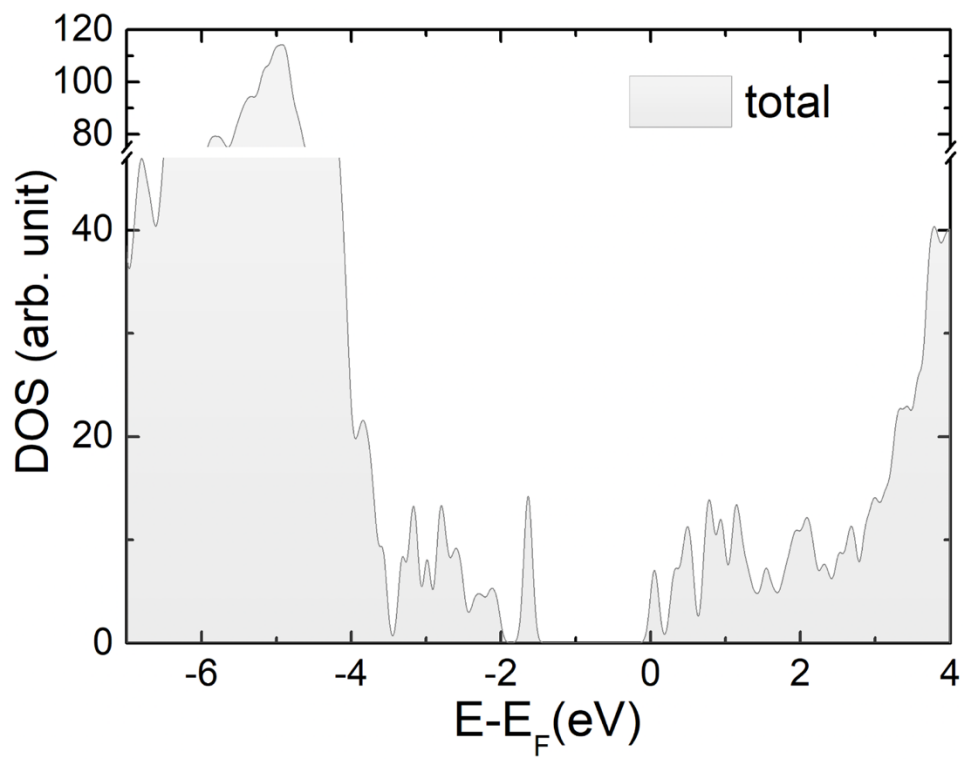


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 88 **Figure S12.** Chronoamperometry results for the first 60 h of the stability experiments in the two-  
 89 electrode configuration under AM 1.5G one-sun illumination 0.5 M H<sub>2</sub>SO<sub>4</sub> in with 0.2 mM Triton  
 90 X-100 at -2.3 V vs. IrO<sub>x</sub>. The photocurrent density reached a saturated value of  $\sim 30$  mA/cm<sup>2</sup> after  
 91  $\sim 40$  h.

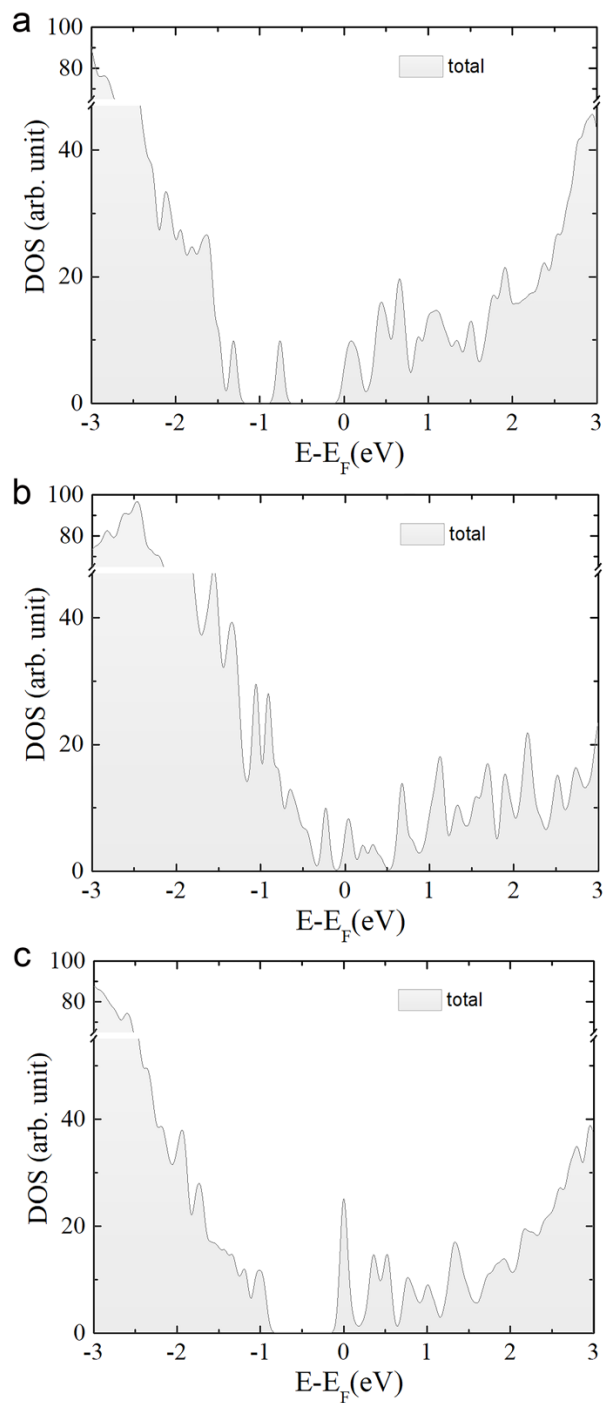
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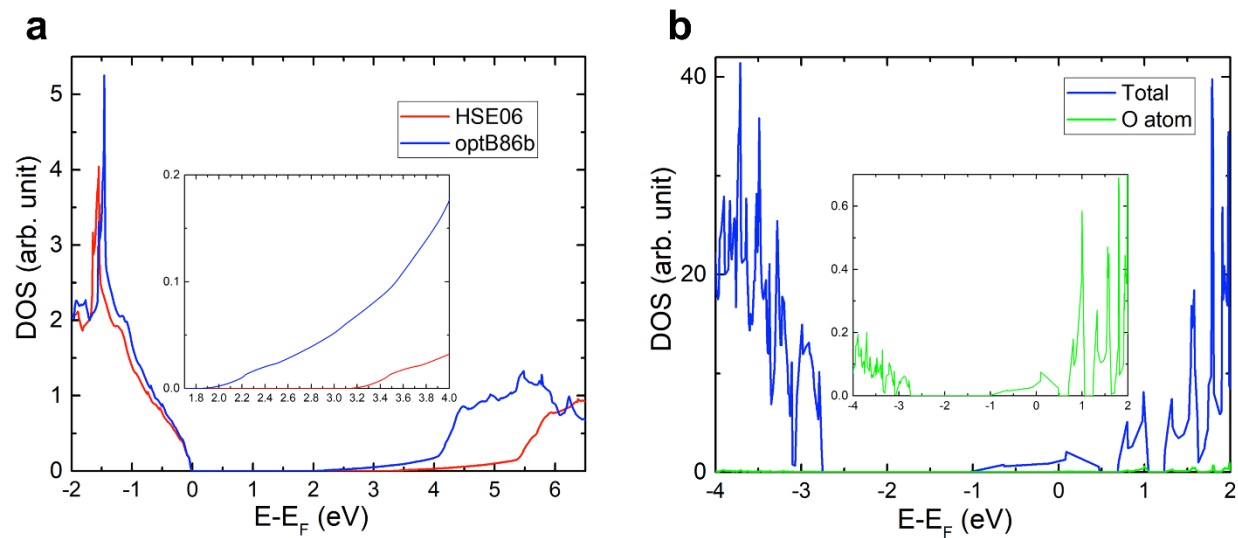
**Figure S13.** (a) Scanning transmission electron microscopy (STEM) image of an  $n^+$ -GaN nanowire at the end of the 3000 h chronoamperometry. No apparent change in nanowire morphology was observed (length  $\sim 600$  nm and diameter  $\sim 100$  nm). Brown boxes represent atomic resolution High-angle annular dark-field STEM images of highly crystalline GaN nanostructure across the wire. (b) Scanning electron micrograph of the  $n^+$ -GaN nanowire on Si photocathode at the end of the 3000 h chronoamperometry. No apparent change in morphology was observed.



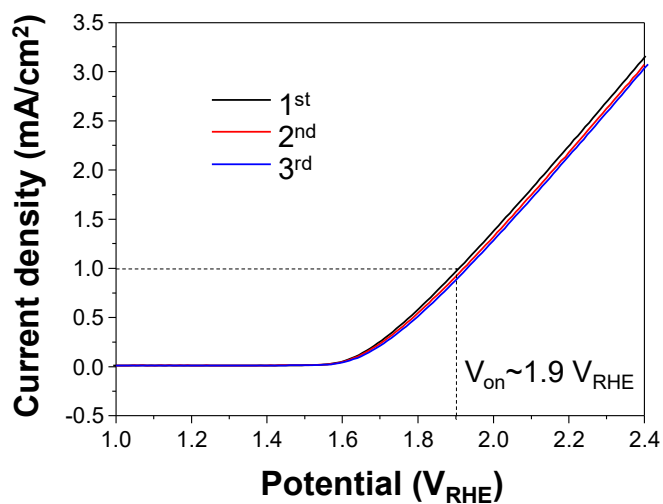
**Figure S14.** Density of states (DOS) of N-rich GaN *m*-plane before oxidation.



**Figure S15.** Density of states (DOS) of metal oxynitride species featured GaN m-plane. (a) – (c) DOS of the first, third and fourth configuration plotted in Figure 5a. Their formation energies are -4.07 eV, -3.95 eV and -2.66 eV, respectively. DOS of the first, third and fourth configurations was calculated with optB86-vdW.



**Figure S16.** Density of states (DOS) of (a) pristine and (b) metal oxynitride featured bulk wz-GaN.



**Figure S17.** Linear sweep voltammetry curves of the IrO<sub>x</sub> counter electrode measured in 0.5 M H<sub>2</sub>SO<sub>4</sub>. Three individual measurements were performed and the averaged onset potential at 1 mA/cm<sup>2</sup> was ~1.9 V<sub>RHE</sub>.

**Table S1.** Comparison between the stability of state-of-the-art photoelectrodes in two- and three-electrode configurations and the GaN nanowires/Si photocathode presented in this work.

| Material                                                                | Photoelectrode      | Stability (Hours) |                 | Ref.             |
|-------------------------------------------------------------------------|---------------------|-------------------|-----------------|------------------|
|                                                                         |                     | Two-Electrode     | Three-Electrode |                  |
| PtRu-GaInP/AlInP/GaInP-GaInP/GaInAs                                     | Photocathode        | 0.4               | 10              | <sup>2</sup>     |
| Rh-TiO <sub>2</sub> -AlInP/GaInP-/GaInAs/GaAs-RuO <sub>x</sub>          | Photocathode        | 0.5               | 30              | <sup>3</sup>     |
| Rh/AlInP-GaInP/GaInAs-RuO <sub>2</sub>                                  | Photocathode        | 0.1               | 40              | <sup>4</sup>     |
| InGaP/GaAs double junction                                              | Photoanode          | 15                | 150             | <sup>5</sup>     |
| 3J a-Si SC with Co/NiMoZn                                               | Photoanode          | 0.2               | 0.5             | <sup>6</sup>     |
| Co-Ci dual doped BiVO <sub>4</sub> /1J perovskite solar cell            | Photoanode          | 12                | <12             | <sup>7</sup>     |
| BiVO <sub>4</sub>   Fe <sub>2</sub> O <sub>3</sub> - 2J Si              | Photoanode          | 8                 | 8               | <sup>8</sup>     |
| Fe <sub>2</sub> O <sub>3</sub> /perovskite tandem cell                  | Photoanode          | 0.95              | 8               | <sup>9</sup>     |
| Pt/GaN/3J GaInP <sub>2</sub> /GaAs/Ge                                   | Photocathode        | 60                | 80              | <sup>10</sup>    |
| Ni-TiO <sub>2</sub> /GaInP/GaAs                                         | Photoanode          | 40                | NA              | <sup>11</sup>    |
| Co-Pi Mn doped Fe <sub>2</sub> O <sub>3</sub> -1J perovskite solar cell | Photoanode          | 8                 | NA              | <sup>12</sup>    |
| Co-Pi Gradient W: BiVO <sub>4</sub> /2J a:Si solar cell                 | Photoanode          | 1                 | NA              | <sup>13</sup>    |
| Pt/GaInP <sub>2</sub> /GaAs                                             | Photocathode        | 10                | NA              | <sup>14</sup>    |
| WO <sub>3</sub> /BiVO <sub>4</sub> -DSSC                                | Photoanode          | 2                 | NA              | <sup>15</sup>    |
| WO <sub>3</sub> /BiVO <sub>4</sub> /GaAs/InGaAsP                        | PV-PEC              | 1                 | NA              | <sup>16</sup>    |
| Pt-TiO <sub>2</sub> -3J-Solar cell                                      | Photocathode        | 2                 | NA              | <sup>17</sup>    |
| CdS/CdSe/DSSC                                                           | Photoanode          | 2                 | NA              | <sup>18</sup>    |
| CoPi/BiVO <sub>4</sub> /p <sup>+</sup> n Si                             | Photoanode          | 1                 | NA              | <sup>19</sup>    |
| Fe <sub>2</sub> O <sub>3</sub> /DSC tandem cell                         | Photoanode          | 8                 | NA              | <sup>20</sup>    |
| Pt/1J InGaN                                                             | Photocathode        | 300               | NA              | <sup>21</sup>    |
| <b>Ga(O)N nanowires/Si</b>                                              | <b>Photocathode</b> | <b>3000</b>       | <b>NA</b>       | <b>This work</b> |

122 **Table S2.** Performance comparison of reported Si photocathodes for H<sub>2</sub> evolution reaction.

| Photocathode                   | Passivation                         | Cocatalyst                                        | Electrolyte                           | Onset potential (V <sub>RHE</sub> ) | Current density at 0.0 V <sub>RHE</sub> (mA/cm <sup>2</sup> ) | Ref.             |
|--------------------------------|-------------------------------------|---------------------------------------------------|---------------------------------------|-------------------------------------|---------------------------------------------------------------|------------------|
| p-Si                           | -                                   | Ni/Fe:In <sub>2</sub> S <sub>3</sub>              | 0.5 M Na <sub>2</sub> SO <sub>3</sub> | 0.44                                | 7.0                                                           | 22               |
| p-Si                           | -                                   | Ni(TEOA) <sub>2</sub> Cl <sub>2</sub>             | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.11                                | 5.6                                                           | 23               |
| Mesoporous p-Si                | -                                   | Co-P                                              | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.3                                 | 23.9                                                          | 24               |
| p-Si microwires                | -                                   | CoS <sub>2</sub>                                  | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.25                                | 3.2                                                           | 25               |
| p-Si                           | -                                   | Mo <sub>3</sub> S <sub>4</sub>                    | 1 M HClO <sub>4</sub>                 | 0.15                                | 8                                                             | 26               |
| p-Si                           | -                                   | MoS <sub>x</sub> Cl <sub>y</sub>                  | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.27                                | 20.6                                                          | 27               |
| p-Si                           | TiO <sub>2</sub>                    | Pt                                                | 1 M HClO <sub>4</sub>                 | 0.48                                | 30                                                            | 28               |
| p-Si                           | TiO <sub>2</sub>                    | MoS <sub>2</sub> /Rh-P                            | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.43                                | 24.1                                                          | 29               |
| p-Si pyramid                   | TiO <sub>2</sub>                    | MoS <sub>1.75</sub> P <sub>0.25</sub>             | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.29                                | 23.8                                                          | 30               |
| n <sup>+</sup> p Si            | -                                   | MoS <sub>2</sub> -Mo <sub>3</sub> S <sub>13</sub> | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.4                                 | 17                                                            | 31               |
| n <sup>+</sup> p Si            | Mo <sub>x</sub> Si/SiO <sub>2</sub> | MoS <sub>2</sub>                                  | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.31                                | 18.5                                                          | 32               |
| n <sup>+</sup> p Si microwires | NiSi                                | NiMo                                              | 1 M KOH                               | 0.55                                | 29.8                                                          | 33               |
| n <sup>+</sup> p Si            | TiO <sub>2</sub>                    | Pt                                                | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.64                                | 20.3                                                          | 34               |
| n <sup>+</sup> p Si            | Al <sub>2</sub> O <sub>3</sub>      | MoS <sub>2</sub>                                  | 1 M HClO <sub>4</sub>                 | 0.4                                 | 35                                                            | 35               |
| n <sup>+</sup> p Si pyramid    | TiO <sub>2</sub>                    | Pt                                                | 1 M HClO <sub>4</sub>                 | 0.6                                 | 35                                                            | 36               |
| n <sup>+</sup> p Si pyramid    | -                                   | MoSe <sub>2</sub>                                 | 1 M HClO <sub>4</sub>                 | 0.4                                 | 27.5                                                          | 37               |
| n <sup>+</sup> p Si            | GaN nanowires                       | Pt                                                | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.56                                | 37                                                            | 38               |
| n <sup>+</sup> p Si            | GaN nanowires                       | MoS <sub>2</sub>                                  | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.4                                 | 40                                                            | 39               |
| n <sup>+</sup> p Si            | GaN quasi-film                      | Pt                                                | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.34                                | 25                                                            | 1                |
| n <sup>+</sup> p Si            | GaN quasi-film                      | -                                                 | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | -0.08                               | 0                                                             |                  |
| n <sup>+</sup> p Si            | GaN nanowires                       | -                                                 | 0.5 M H <sub>2</sub> SO <sub>4</sub>  | 0.4                                 | 30                                                            | <b>This work</b> |

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124 **Table S3.** Summary table showing average  $V_{on}$  and average  $J_{ph}$  during different cycles of the long-  
125 term stability experiments.

| Start of cycle (h) | End of cycle (h) | Average $V_{on}$ (V vs. $IrO_x$ ) | Average $ J_{ph} $ at -2.3 V vs. $IrO_x$ (mA/cm <sup>2</sup> ) |
|--------------------|------------------|-----------------------------------|----------------------------------------------------------------|
| 0                  | 100              | -1.5                              | 28.3                                                           |
| 100                | 200              | -1.35                             | 29                                                             |
| 200                | 300              | -1.4                              | 29.1                                                           |
| 300                | 400              | -1.42                             | 29.5                                                           |
| 400                | 500              | -1.4                              | 29                                                             |
| 500                | 600              | -1.38                             | 30.4                                                           |
| 600                | 700              | -1.4                              | 30.2                                                           |
| 700                | 800              | -1.43                             | 30.8                                                           |
| 800                | 900              | -1.4                              | 30.6                                                           |
| 900                | 1000             | -1.39                             | 30                                                             |
| 1000               | 1100             | -1.41                             | 29.8                                                           |
| 1100               | 1200             | -1.4                              | 29.4                                                           |
| 1200               | 1300             | -1.38                             | 30.8                                                           |
| 1300               | 1400             | -1.35                             | 30.1                                                           |
| 1400               | 1500             | -1.35                             | 30.4                                                           |
| 1500               | 1600             | -1.38                             | 30.5                                                           |
| 1600               | 1700             | -1.4                              | 30.2                                                           |
| 1700               | 1800             | -1.41                             | 29.9                                                           |
| 1800               | 1900             | -1.38                             | 30.5                                                           |
| 1900               | 2000             | -1.43                             | 30.1                                                           |
| 2000               | 2100             | -1.4                              | 30                                                             |
| 2100               | 2200             | -1.42                             | 30.7                                                           |
| 2200               | 2300             | -1.38                             | 30.1                                                           |
| 2300               | 2400             | -1.39                             | 29.5                                                           |
| 2400               | 2500             | -1.43                             | 29.4                                                           |
| 2500               | 2600             | -1.4                              | 30.4                                                           |
| 2600               | 2700             | -1.4                              | 30.2                                                           |
| 2700               | 2800             | -1.39                             | 30.6                                                           |
| 2800               | 2900             | -1.4                              | 29.7                                                           |
| 2900               | 3000             | -1.42                             | 28                                                             |

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128 **Table S4.** Summary of state-of-the-art metal oxynitrides and their stability under solar water  
 129 splitting conditions.

| Material                                                                | Electrolyte                                        | Stability   | pH          | Ref.             |
|-------------------------------------------------------------------------|----------------------------------------------------|-------------|-------------|------------------|
| TaON                                                                    | Na <sub>2</sub> SO <sub>4</sub>                    | <3 h        | 8           | <sup>21</sup>    |
| TiON                                                                    | 0.1 M KOH                                          | NA          | 14          | <sup>22</sup>    |
| (Ga <sub>1-x</sub> Zn <sub>x</sub> )(N <sub>1-x</sub> O <sub>x</sub> )  | H <sub>2</sub> SO <sub>4</sub> + NaNO <sub>2</sub> | 35          | 4.5         | <sup>23</sup>    |
| LaTiO <sub>2</sub> N                                                    | 10 mM AgNO <sub>3</sub>                            | 40          | 8           | <sup>23,24</sup> |
| LaMg <sub>x</sub> Ta <sub>1-x</sub> O <sub>1+3x</sub> N <sub>2-3x</sub> | H <sub>2</sub> O                                   | 48          | 8           | <sup>25</sup>    |
| GaON                                                                    | 0.5M Na <sub>2</sub> SO <sub>4</sub>               | NA          | 7           | <sup>26</sup>    |
| <b>Ga(O)N/Si</b>                                                        | <b>0.5M H<sub>2</sub>SO<sub>4</sub></b>            | <b>3000</b> | <b>0.16</b> | <b>This work</b> |

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132 **Table S5.** ICP-MS measurements of Ga element at different durations during the 3,000 h stability  
133 test.

| Time (Hours) | Ga (nmol) |
|--------------|-----------|
| 500-524      | 12.21     |
| 1000-1024    | 11.18     |
| 2000-2024    | 11.18     |
| 2980-3000    | 11.18     |

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**Table S6.** Formation energy for GaON species on N-rich and pristine GaN *m*-plane for the second configuration in Figure 5(a). In general, metal-O bonds are stronger than metal-N bonds. This is because oxygen is more electronegative than nitrogen, meaning that it attracts electrons more strongly. As a result, the metal-O bond is more polarized and the oxygen atom carries a partial negative charge, while the metal carries a partial positive charge. This polarization leads to a stronger bond. Additionally, oxygen is a smaller atom than nitrogen, so the metal-O bond is also shorter and stronger due to the stronger overlap of atomic orbitals.

|                        | Formation energy (eV) |              |
|------------------------|-----------------------|--------------|
|                        | O-N replacement       | O adsorption |
| N-rich <i>m</i> -plane | -4.29                 | -4.19        |
| <i>m</i> -plane        | -3.14                 | -1.13        |

## References

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